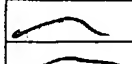



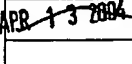
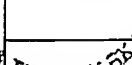
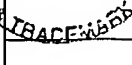
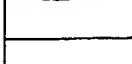
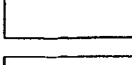
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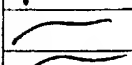
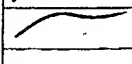
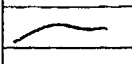
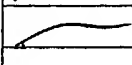
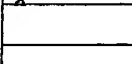
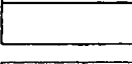
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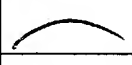


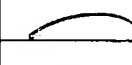
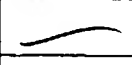



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	C03	"Challenges of electroplated Copper Film and Device Characteristics for Copper Slurry Design, Maria L. Peterson et al., Semiconductor Fab Tech, Oct. 19, 1999, 5 pages
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EXAMINER

DATE CONSIDERED

8/17/07

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.